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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	5831
Number of Logic Elements/Cells	74637
Total RAM Bits	3170304
Number of I/O	280
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc6slx75-2fg484c

Table 2: Recommended Operating Conditions⁽¹⁾

Symbol	Description			Min	Typ	Max	Units
V _{CCINT}	Internal supply voltage relative to GND	-3, -3N, -2	Standard performance ⁽²⁾	1.14	1.2	1.26	V
		-3, -2	Extended performance ⁽²⁾	1.2	1.23	1.26	V
		-1L	Standard performance ⁽²⁾	0.95	1.0	1.05	V
V _{CCAUX} ⁽³⁾⁽⁴⁾	Auxiliary supply voltage relative to GND	V _{CCAUX} = 2.5V ⁽⁵⁾		2.375	2.5	2.625	V
		V _{CCAUX} = 3.3V		3.15	3.3	3.45	V
V _{CCO} ⁽⁶⁾⁽⁷⁾⁽⁸⁾	Output supply voltage relative to GND			1.1	–	3.45	V
V _{IN}	Input voltage relative to GND	All I/O standards (except PCI)	Commercial temperature (C)	–0.5	–	4.0	V
			Industrial temperature (I)	–0.5	–	3.95	V
			Expanded (Q) temperature	–0.5	–	3.95	V
		PCI I/O standard ⁽⁹⁾		–0.5	–	V _{CCO} + 0.5	V
I _{IN} ⁽¹⁰⁾	Maximum current through pin using PCI I/O standard when forward biasing the clamp diode. ⁽⁹⁾	Commercial (C) and Industrial temperature (I)		–	–	10	mA
		Expanded (Q) temperature		–	–	7	mA
V _{BATT} ⁽¹¹⁾	Battery voltage relative to GND, T _j = 0°C to +85°C (LX75, LX75T, LX100, LX100T, LX150, and LX150T only)			1.0	–	3.6	V
T _j	Junction temperature operating range	Commercial (C) range		0	–	85	°C
		Industrial temperature (I) range		–40	–	100	°C
		Expanded (Q) temperature range		–40	–	125	°C

Notes:

- All voltages are relative to ground.
- See *Interface Performances for Memory Interfaces* in Table 25. The extended performance range is specified for designs not using the standard V_{CCINT} voltage range. The standard V_{CCINT} voltage range is used for:
 - Designs that do not use an MCB
 - LX4 devices
 - Devices in the TQG144 or CPG196 packages
 - Devices with the -3N speed grade
- Recommended maximum voltage droop for V_{CCAUX} is 10 mV/ms.
- During configuration, if V_{CCO_2} is 1.8V, then V_{CCAUX} must be 2.5V.
- The -1L devices require $V_{CCAUX} = 2.5V$ when using the LVDS_25, LVDS_33, BLVDS_25, LVPECL_25, RSDS_25, RSDS_33, PPDS_25, and PPDS_33 I/O standards on inputs. LVPECL_33 is not supported in the -1L devices.
- Configuration data is retained even if V_{CCO} drops to 0V.
- Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
- For PCI systems, the transmitter and receiver should have common supplies for V_{CCO} .
- Devices with a -1L speed grade do not support Xilinx PCI IP.
- Do not exceed a total of 100 mA per bank.
- V_{BATT} is required to maintain the battery backed RAM (BBR) AES key when V_{CCAUX} is not applied. Once V_{CCAUX} is applied, V_{BATT} can be unconnected. When BBR is not used, Xilinx recommends connecting to V_{CCAUX} or GND. However, V_{BATT} can be unconnected.

Table 4: DC Characteristics Over Recommended Operating Conditions

Symbol	Description		Min	Typ	Max	Units
$V_{DRI\text{NT}}$	Data retention V_{CCINT} voltage (below which configuration data might be lost)		0.8	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)		2.0	–	–	V
I_{REF}	V_{REF} leakage current per pin for commercial (C) and industrial (I) devices		–10	–	10	μA
	V_{REF} leakage current per pin for expanded (Q) devices		–15	–	15	μA
I_L	Input or output leakage current per pin (sample-tested) for commercial (C) and industrial (I) devices		–10	–	10	μA
	Input or output leakage current per pin (sample-tested) for expanded (Q) devices		–15	–	15	μA
I_{HS}	Leakage current on pins during hot socketing with FPGA unpowered	All pins except PROGRAM_B, DONE, and JTAG pins when HSWAPEN = 1	–20	–	20	μA
		PROGRAM_B, DONE, and JTAG pins, or other pins when HSWAPEN = 0	$I_{HS} + I_{RPU}$			μA
$C_{IN}^{(1)}$	Die input capacitance at the pad		–	–	10	pF
I_{RPU}	Pad pull-up (when selected) @ $V_{IN} = 0\text{V}$, $V_{CCO} = 3.3\text{V}$ or $V_{CCAUX} = 3.3\text{V}$		200	–	500	μA
	Pad pull-up (when selected) @ $V_{IN} = 0\text{V}$, $V_{CCO} = 2.5\text{V}$ or $V_{CCAUX} = 2.5\text{V}$		120	–	350	μA
	Pad pull-up (when selected) @ $V_{IN} = 0\text{V}$, $V_{CCO} = 1.8\text{V}$		60	–	200	μA
	Pad pull-up (when selected) @ $V_{IN} = 0\text{V}$, $V_{CCO} = 1.5\text{V}$		40	–	150	μA
	Pad pull-up (when selected) @ $V_{IN} = 0\text{V}$, $V_{CCO} = 1.2\text{V}$		12	–	100	μA
I_{RPD}	Pad pull-down (when selected) @ $V_{IN} = V_{CCO}$, $V_{CCAUX} = 3.3\text{V}$		200	–	550	μA
	Pad pull-down (when selected) @ $V_{IN} = V_{CCO}$, $V_{CCAUX} = 2.5\text{V}$		140	–	400	μA
$I_{BATT}^{(2)}$	Battery supply current		–	–	150	nA
$R_{DT}^{(3)}$	Resistance of optional input differential termination circuit, $V_{CCAUX} = 3.3\text{V}$		–	100	–	Ω
$R_{IN_TERM}^{(5)}$	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_25) for commercial (C) and industrial (I) devices		23	25	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_25) for expanded (Q) devices		20	25	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_50) for commercial (C) and industrial (I) devices		39	50	72	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_50) for expanded (Q) devices		32	50	74	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_75) for commercial (C) and industrial (I) devices		56	75	109	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_75) for expanded (Q) devices		47	75	115	Ω
R_{OUT_TERM}	Thevenin equivalent resistance of programmable output termination (UNTUNED_25)		11	25	52	Ω
	Thevenin equivalent resistance of programmable output termination (UNTUNED_50)		21	50	96	Ω
	Thevenin equivalent resistance of programmable output termination (UNTUNED_75)		29	75	145	Ω

Notes:

1. The C_{IN} measurement represents the die capacitance at the pad, not including the package.
2. Maximum value specified for worst case process at 25°C. LX75, LX75T, LX100, LX100T, LX150, and LX150T only.
3. Refer to IBIS models for R_{DT} variation and for values at $V_{CCAUX} = 2.5\text{V}$. IBIS values for R_{DT} are valid for all temperature ranges.
4. V_{CCO2} is not required for data retention. The minimum V_{CCO2} for power-on reset and configuration is 1.65V.
5. Termination resistance to a $V_{CCO}/2$ level.

Table 8: Recommended Operating Conditions for User I/Os Using Differential Signal Standards

I/O Standard	V _{CCO} for Drivers		
	V, Min	V, Nom	V, Max
LVDS_33	3.0	3.3	3.45
LVDS_25	2.25	2.5	2.75
BLVDS_25	2.25	2.5	2.75
MINI_LVDS_33	3.0	3.3	3.45
MINI_LVDS_25	2.25	2.5	2.75
LVPECL_33 ⁽¹⁾	N/A—Inputs Only		
LVPECL_25	N/A—Inputs Only		
RSDS_33	3.0	3.3	3.45
RSDS_25	2.25	2.5	2.75
TMDS_33 ⁽¹⁾	3.14	3.3	3.45
PPDS_33	3.0	3.3	3.45
PPDS_25	2.25	2.5	2.75
DISPLAY_PORT	2.3	2.5	2.7
DIFF_MOBILE_DDR	1.7	1.8	1.9
DIFF_HSTL_I	1.4	1.5	1.6
DIFF_HSTL_II	1.4	1.5	1.6
DIFF_HSTL_III	1.4	1.5	1.6
DIFF_HSTL_I_18	1.7	1.8	1.9
DIFF_HSTL_II_18	1.7	1.8	1.9
DIFF_HSTL_III_18	1.7	1.8	1.9
DIFF_SSTL3_I	3.0	3.3	3.45
DIFF_SSTL3_II	3.0	3.3	3.45
DIFF_SSTL2_I	2.3	2.5	2.7
DIFF_SSTL2_II	2.3	2.5	2.7
DIFF_SSTL18_I	1.7	1.8	1.9
DIFF_SSTL18_II	1.7	1.8	1.9
DIFF_SSTL15_II	1.425	1.5	1.575

Notes:

1. LVPECL_33 and TMDS_33 inputs require V_{CCAUX} = 3.3V nominal.

eFUSE Read Endurance

Table 11 lists the minimum guaranteed number of read cycle operations for Device DNA and for the AES eFUSE key. For more information, see [UG380: Spartan-6 FPGA Configuration User Guide](#).

Table 11: eFUSE Read Endurance

Symbol	Description	Speed Grade				Units (Min)
		-3	-3N	-2	-1L	
DNA_CYCLES	Number of DNA_PORT READ operations or JTAG ISC_DNA read command operations. Unaffected by SHIFT operations.	30,000,000				Read Cycles
AES_CYCLES	Number of JTAG FUSE_KEY or FUSE_CNTL read command operations. Unaffected by SHIFT operations.	30,000,000				Read Cycles

GTP Transceiver Specifications

GTP transceivers are available in the Spartan-6 LXT devices. See [DS160: Spartan-6 Family Overview](#) for more information.

GTP Transceiver DC Characteristics

Table 12: Absolute Maximum Ratings for GTP Transceivers⁽¹⁾

Symbol	Description	Min	Max	Units
MGTAVCC	Analog supply voltage for the GTP transmitter and receiver circuits relative to GND	-0.5	1.32	V
MGTAVTTTX	Analog supply voltage for the GTP transmitter termination circuit relative to GND	-0.5	1.32	V
MGTAVTTRX	Analog supply voltage for the GTP receiver termination circuit relative to GND	-0.5	1.32	V
MGTAVCCPLL	Analog supply voltage for the GTP transmitter and receiver PLL circuits relative to GND	-0.5	1.32	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTP transceiver bank (top or bottom)	-0.5	1.32	V
V _{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	-0.5	1.32	V
V _{MGTREFCLK}	Reference clock absolute input voltage	-0.5	1.32	V

Notes:

- Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.

Table 13: Recommended Operating Conditions for GTP Transceivers⁽¹⁾⁽²⁾⁽³⁾

Symbol	Description	Min	Typ	Max	Units
MGTAVCC	Analog supply voltage for the GTP transmitter and receiver circuits relative to GND	1.14	1.20	1.26	V
MGTAVTTTX	Analog supply voltage for the GTP transmitter termination circuit relative to GND	1.14	1.20	1.26	V
MGTAVTTRX	Analog supply voltage for the GTP receiver termination circuit relative to GND	1.14	1.20	1.26	V
MGTAVCCPLL	Analog supply voltage for the GTP transmitter and receiver PLL circuits relative to GND	1.14	1.20	1.26	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTP transceiver bank (top or bottom)	1.14	1.20	1.26	V

Notes:

- Each voltage listed requires the filter circuit described in [UG386: Spartan-6 FPGA GTP Transceivers User Guide](#).
- Voltages are specified for the temperature range of T_j = -40°C to +125°C.
- The voltage level of MGTAVCCPLL must not exceed the voltage level of MGTAVCC +10mV. The voltage level of MGTAVCC must not exceed the voltage level of MGTAVCCPLL.

Production Silicon and ISE Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases. [Table 27](#) lists the production released Spartan-6 family member, speed grade, and the minimum corresponding supported speed specification version and ISE® software revisions. The ISE software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 27: Spartan-6 Device Production Software and Speed Specification Release⁽¹⁾

Device	Speed Grade Designations ⁽²⁾			
	-3 ⁽³⁾	-3N	-2 ⁽⁴⁾	-1L
XC6SLX4	ISE 12.4 v1.15	N/A	ISE 12.3 v1.12 ⁽⁵⁾	ISE 13.2 v1.07
XC6SLX9	ISE 12.4 v1.15	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 12.3 v1.12 ⁽⁵⁾	ISE 13.2 v1.07
XC6SLX16	ISE 12.1 v1.08	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 11.5 v1.06	ISE 13.2 v1.07
XC6SLX25	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.2 v1.07
XC6SLX25T	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 12.2 v1.11 ⁽⁶⁾	N/A
XC6SLX45	ISE 12.1 v1.08	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 11.5 v1.07	ISE 13.1 v1.06
XC6SLX45T	ISE 12.1 v1.08	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 12.1 v1.08	N/A
XC6SLX75	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.2 v1.07
XC6SLX75T	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 12.2 v1.11 ⁽⁶⁾	N/A
XC6SLX100	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.1 v1.06
XC6SLX100T	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 12.2 v1.11 ⁽⁶⁾	N/A
XC6SLX150	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.1 v1.06
XC6SLX150T	ISE 12.2 v1.11 ⁽⁶⁾	ISE 13.1 Update v1.18 ⁽⁷⁾	ISE 12.2 v1.11 ⁽⁶⁾	N/A
XA6SLX4	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX9	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX16	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX25	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX25T	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX45	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX45T	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX75	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX75T	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX100	N/A	N/A	ISE 13.3 v1.20	N/A

Table 28: IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices (Cont'd)

I/O Standard	T _{IOPI}				T _{IOOP}				T _{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L ⁽¹⁾	-3	-3N	-2	-1L ⁽¹⁾	-3	-3N	-2	-1L ⁽¹⁾	
LVC MOS33, Fast, 8 mA	1.34	1.46	1.59	1.82	2.07	2.21	2.41	3.03	2.07	2.21	2.41	3.03	ns
LVC MOS33, Fast, 12 mA	1.34	1.46	1.59	1.82	1.65	1.79	1.99	2.62	1.65	1.79	1.99	2.62	ns
LVC MOS33, Fast, 16 mA	1.34	1.46	1.59	1.82	1.65	1.79	1.99	2.62	1.65	1.79	1.99	2.62	ns
LVC MOS33, Fast, 24 mA	1.34	1.46	1.59	1.82	1.65	1.79	1.99	2.62	1.65	1.79	1.99	2.62	ns
LVC MOS25, QUIETIO, 2 mA	0.82	0.94	1.07	1.31	4.81	4.95	5.15	5.79	4.81	4.95	5.15	5.79	ns
LVC MOS25, QUIETIO, 4 mA	0.82	0.94	1.07	1.31	3.70	3.84	4.04	4.66	3.70	3.84	4.04	4.66	ns
LVC MOS25, QUIETIO, 6 mA	0.82	0.94	1.07	1.31	3.46	3.60	3.80	4.38	3.46	3.60	3.80	4.38	ns
LVC MOS25, QUIETIO, 8 mA	0.82	0.94	1.07	1.31	3.20	3.34	3.54	4.12	3.20	3.34	3.54	4.12	ns
LVC MOS25, QUIETIO, 12 mA	0.82	0.94	1.07	1.31	2.83	2.97	3.17	3.75	2.83	2.97	3.17	3.75	ns
LVC MOS25, QUIETIO, 16 mA	0.82	0.94	1.07	1.31	2.64	2.78	2.98	3.64	2.64	2.78	2.98	3.64	ns
LVC MOS25, QUIETIO, 24 mA	0.82	0.94	1.07	1.31	2.45	2.59	2.79	3.42	2.45	2.59	2.79	3.42	ns
LVC MOS25, Slow, 2 mA	0.82	0.94	1.07	1.31	3.78	3.92	4.12	4.76	3.78	3.92	4.12	4.76	ns
LVC MOS25, Slow, 4 mA	0.82	0.94	1.07	1.31	2.79	2.93	3.13	3.73	2.79	2.93	3.13	3.73	ns
LVC MOS25, Slow, 6 mA	0.82	0.94	1.07	1.31	2.73	2.87	3.07	3.66	2.73	2.87	3.07	3.66	ns
LVC MOS25, Slow, 8 mA	0.82	0.94	1.07	1.31	2.48	2.62	2.82	3.42	2.48	2.62	2.82	3.42	ns
LVC MOS25, Slow, 12 mA	0.82	0.94	1.07	1.31	2.01	2.15	2.35	2.95	2.01	2.15	2.35	2.95	ns
LVC MOS25, Slow, 16 mA	0.82	0.94	1.07	1.31	2.01	2.15	2.35	2.95	2.01	2.15	2.35	2.95	ns
LVC MOS25, Slow, 24 mA	0.82	0.94	1.07	1.31	2.01	2.15	2.35	2.94	2.01	2.15	2.35	2.94	ns
LVC MOS25, Fast, 2 mA	0.82	0.94	1.07	1.31	3.35	3.49	3.69	4.31	3.35	3.49	3.69	4.31	ns
LVC MOS25, Fast, 4 mA	0.82	0.94	1.07	1.31	2.25	2.39	2.59	3.22	2.25	2.39	2.59	3.22	ns
LVC MOS25, Fast, 6 mA	0.82	0.94	1.07	1.31	2.09	2.23	2.43	3.05	2.09	2.23	2.43	3.05	ns
LVC MOS25, Fast, 8 mA	0.82	0.94	1.07	1.31	2.02	2.16	2.36	2.98	2.02	2.16	2.36	2.98	ns
LVC MOS25, Fast, 12 mA	0.82	0.94	1.07	1.31	1.56	1.70	1.90	2.52	1.56	1.70	1.90	2.52	ns
LVC MOS25, Fast, 16 mA	0.82	0.94	1.07	1.31	1.56	1.70	1.90	2.52	1.56	1.70	1.90	2.52	ns
LVC MOS25, Fast, 24 mA	0.82	0.94	1.07	1.31	1.56	1.70	1.90	2.52	1.56	1.70	1.90	2.52	ns
LVC MOS18, QUIETIO, 2 mA	1.18	1.30	1.43	2.04	5.92	6.06	6.26	6.80	5.92	6.06	6.26	6.80	ns
LVC MOS18, QUIETIO, 4 mA	1.18	1.30	1.43	2.04	4.74	4.88	5.08	5.63	4.74	4.88	5.08	5.63	ns
LVC MOS18, QUIETIO, 6 mA	1.18	1.30	1.43	2.04	4.05	4.19	4.39	4.96	4.05	4.19	4.39	4.96	ns
LVC MOS18, QUIETIO, 8 mA	1.18	1.30	1.43	2.04	3.71	3.85	4.05	4.63	3.71	3.85	4.05	4.63	ns
LVC MOS18, QUIETIO, 12 mA	1.18	1.30	1.43	2.04	3.35	3.49	3.69	4.27	3.35	3.49	3.69	4.27	ns
LVC MOS18, QUIETIO, 16 mA	1.18	1.30	1.43	2.04	3.20	3.34	3.54	4.14	3.20	3.34	3.54	4.14	ns
LVC MOS18, QUIETIO, 24 mA	1.18	1.30	1.43	2.04	2.96	3.10	3.30	3.98	2.96	3.10	3.30	3.98	ns
LVC MOS18, Slow, 2 mA	1.18	1.30	1.43	2.04	4.62	4.76	4.96	5.54	4.62	4.76	4.96	5.54	ns
LVC MOS18, Slow, 4 mA	1.18	1.30	1.43	2.04	3.69	3.83	4.03	4.60	3.69	3.83	4.03	4.60	ns
LVC MOS18, Slow, 6 mA	1.18	1.30	1.43	2.04	3.00	3.14	3.34	3.94	3.00	3.14	3.34	3.94	ns
LVC MOS18, Slow, 8 mA	1.18	1.30	1.43	2.04	2.19	2.33	2.53	3.17	2.19	2.33	2.53	3.17	ns
LVC MOS18, Slow, 12 mA	1.18	1.30	1.43	2.04	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVC MOS18, Slow, 16 mA	1.18	1.30	1.43	2.04	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns

Table 28: IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices (Cont'd)

I/O Standard	T _{IOPI}				T _{IOOP}				T _{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L ⁽¹⁾	-3	-3N	-2	-1L ⁽¹⁾	-3	-3N	-2	-1L ⁽¹⁾	
LVC MOS12, Fast, 2 mA	0.91	1.03	1.16	1.51	3.46	3.60	3.80	4.44	3.46	3.60	3.80	4.44	ns
LVC MOS12, Fast, 4 mA	0.91	1.03	1.16	1.51	2.35	2.49	2.69	3.30	2.35	2.49	2.69	3.30	ns
LVC MOS12, Fast, 6 mA	0.91	1.03	1.16	1.51	1.79	1.93	2.13	2.75	1.79	1.93	2.13	2.75	ns
LVC MOS12, Fast, 8 mA	0.91	1.03	1.16	1.51	1.68	1.82	2.02	2.64	1.68	1.82	2.02	2.64	ns
LVC MOS12, Fast, 12 mA	0.91	1.03	1.16	1.51	1.66	1.80	2.00	2.62	1.66	1.80	2.00	2.62	ns
LVC MOS12_JEDEC, QUIETIO, 2 mA	1.50	1.62	1.75	1.88	6.39	6.53	6.73	7.31	6.39	6.53	6.73	7.31	ns
LVC MOS12_JEDEC, QUIETIO, 4 mA	1.50	1.62	1.75	1.88	4.98	5.12	5.32	5.88	4.98	5.12	5.32	5.88	ns
LVC MOS12_JEDEC, QUIETIO, 6 mA	1.50	1.62	1.75	1.88	4.67	4.81	5.01	5.54	4.67	4.81	5.01	5.54	ns
LVC MOS12_JEDEC, QUIETIO, 8 mA	1.50	1.62	1.75	1.88	4.23	4.37	4.57	5.22	4.23	4.37	4.57	5.22	ns
LVC MOS12_JEDEC, QUIETIO, 12 mA	1.50	1.62	1.75	1.88	3.99	4.13	4.33	4.94	3.99	4.13	4.33	4.94	ns
LVC MOS12_JEDEC, Slow, 2 mA	1.50	1.62	1.75	1.88	5.00	5.14	5.34	5.90	5.00	5.14	5.34	5.90	ns
LVC MOS12_JEDEC, Slow, 4 mA	1.50	1.62	1.75	1.88	2.85	2.99	3.19	3.80	2.85	2.99	3.19	3.80	ns
LVC MOS12_JEDEC, Slow, 6 mA	1.50	1.62	1.75	1.88	2.76	2.90	3.10	3.72	2.76	2.90	3.10	3.72	ns
LVC MOS12_JEDEC, Slow, 8 mA	1.50	1.62	1.75	1.88	2.35	2.49	2.69	3.30	2.35	2.49	2.69	3.30	ns
LVC MOS12_JEDEC, Slow, 12 mA	1.50	1.62	1.75	1.88	2.09	2.23	2.43	3.05	2.09	2.23	2.43	3.05	ns
LVC MOS12_JEDEC, Fast, 2 mA	1.50	1.62	1.75	1.88	3.46	3.60	3.80	4.42	3.46	3.60	3.80	4.42	ns
LVC MOS12_JEDEC, Fast, 4 mA	1.50	1.62	1.75	1.88	2.35	2.49	2.69	3.31	2.35	2.49	2.69	3.31	ns
LVC MOS12_JEDEC, Fast, 6 mA	1.50	1.62	1.75	1.88	1.79	1.93	2.13	2.76	1.79	1.93	2.13	2.76	ns
LVC MOS12_JEDEC, Fast, 8 mA	1.50	1.62	1.75	1.88	1.69	1.83	2.03	2.65	1.69	1.83	2.03	2.65	ns
LVC MOS12_JEDEC, Fast, 12 mA	1.50	1.62	1.75	1.88	1.66	1.80	2.00	2.62	1.66	1.80	2.00	2.62	ns

Notes:

1. The -1L values listed in this table are also applicable to the Spartan-6Q devices.
2. Devices with a -1L speed grade do not support Xilinx PCI IP.

Table 29: IOB Switching Characteristics for the Automotive XA Spartan-6 and the Spartan-6Q Devices⁽¹⁾ (Cont'd)

I/O Standard	T _{IOPI}		T _{IOOP}		T _{IOTP}		Units
	Speed Grade		Speed Grade		Speed Grade		
	-3	-2	-3	-2	-3	-2	
LVC MOS15, QUIETIO, 2 mA	1.05	1.23	5.63	5.83	5.63	5.83	ns
LVC MOS15, QUIETIO, 4 mA	1.05	1.23	4.75	4.95	4.75	4.95	ns
LVC MOS15, QUIETIO, 6 mA	1.05	1.23	4.21	4.41	4.21	4.41	ns
LVC MOS15, QUIETIO, 8 mA	1.05	1.23	4.05	4.25	4.05	4.25	ns
LVC MOS15, QUIETIO, 12 mA	1.05	1.23	3.74	3.94	3.74	3.94	ns
LVC MOS15, QUIETIO, 16 mA	1.05	1.23	3.52	3.72	3.52	3.72	ns
LVC MOS15, Slow, 2 mA	1.05	1.23	4.32	4.52	4.32	4.52	ns
LVC MOS15, Slow, 4 mA	1.05	1.23	3.58	3.78	3.58	3.78	ns
LVC MOS15, Slow, 6 mA	1.05	1.23	2.45	2.65	2.45	2.65	ns
LVC MOS15, Slow, 8 mA	1.05	1.23	2.46	2.66	2.46	2.66	ns
LVC MOS15, Slow, 12 mA	1.05	1.23	2.17	2.37	2.17	2.37	ns
LVC MOS15, Slow, 16 mA	1.05	1.23	2.15	2.35	2.15	2.35	ns
LVC MOS15, Fast, 2 mA	1.05	1.23	3.43	3.63	3.43	3.63	ns
LVC MOS15, Fast, 4 mA	1.05	1.23	2.42	2.62	2.42	2.62	ns
LVC MOS15, Fast, 6 mA	1.05	1.23	1.92	2.12	1.92	2.12	ns
LVC MOS15, Fast, 8 mA	1.05	1.23	1.87	2.07	1.87	2.07	ns
LVC MOS15, Fast, 12 mA	1.05	1.23	1.87	2.07	1.87	2.07	ns
LVC MOS15, Fast, 16 mA	1.05	1.23	1.87	2.07	1.87	2.07	ns
LVC MOS15_JEDEC, QUIETIO, 2 mA	1.10	1.28	5.64	5.84	5.64	5.84	ns
LVC MOS15_JEDEC, QUIETIO, 4 mA	1.10	1.28	4.75	4.95	4.75	4.95	ns
LVC MOS15_JEDEC, QUIETIO, 6 mA	1.10	1.28	4.21	4.41	4.21	4.41	ns
LVC MOS15_JEDEC, QUIETIO, 8 mA	1.10	1.28	4.06	4.26	4.06	4.26	ns
LVC MOS15_JEDEC, QUIETIO, 12 mA	1.10	1.28	3.75	3.95	3.75	3.95	ns
LVC MOS15_JEDEC, QUIETIO, 16 mA	1.10	1.28	3.53	3.73	3.53	3.73	ns
LVC MOS15_JEDEC, Slow, 2 mA	1.10	1.28	4.32	4.52	4.32	4.52	ns
LVC MOS15_JEDEC, Slow, 4 mA	1.10	1.28	3.56	3.76	3.56	3.76	ns
LVC MOS15_JEDEC, Slow, 6 mA	1.10	1.28	2.44	2.64	2.44	2.64	ns
LVC MOS15_JEDEC, Slow, 8 mA	1.10	1.28	2.47	2.67	2.47	2.67	ns
LVC MOS15_JEDEC, Slow, 12 mA	1.10	1.28	2.15	2.35	2.15	2.35	ns
LVC MOS15_JEDEC, Slow, 16 mA	1.10	1.28	2.15	2.35	2.15	2.35	ns
LVC MOS15_JEDEC, Fast, 2 mA	1.10	1.28	3.43	3.63	3.43	3.63	ns
LVC MOS15_JEDEC, Fast, 4 mA	1.10	1.28	2.42	2.62	2.42	2.62	ns
LVC MOS15_JEDEC, Fast, 6 mA	1.10	1.28	1.92	2.12	1.92	2.12	ns
LVC MOS15_JEDEC, Fast, 8 mA	1.10	1.28	1.87	2.07	1.87	2.07	ns
LVC MOS15_JEDEC, Fast, 12 mA	1.10	1.28	1.87	2.07	1.87	2.07	ns
LVC MOS15_JEDEC, Fast, 16 mA	1.10	1.28	1.87	2.07	1.87	2.07	ns
LVC MOS12, QUIETIO, 2 mA	0.98	1.16	6.54	6.74	6.54	6.74	ns
LVC MOS12, QUIETIO, 4 mA	0.98	1.16	5.12	5.32	5.12	5.32	ns

Table 33: Spartan-6 FPGA V_{CCO}/GND Pairs per Bank

Package	Devices	Description	Bank 0	Bank 1	Bank 2	Bank 3	Bank 4	Bank 5
TQG144	LX	V _{CCO} /GND Pairs	3	3	2	3	N/A	N/A
		Maximum I/O per Pair	8	8	13	8	N/A	N/A
CPG196	LX	V _{CCO} /GND Pairs	4	6	4	6	N/A	N/A
		Maximum I/O per Pair	6	4	7	4	N/A	N/A
CSG225	LX	V _{CCO} /GND Pairs	4	4	4	4	N/A	N/A
		Maximum I/O per Pair	10	10	9	10	N/A	N/A
FT(G)256	LX	V _{CCO} /GND Pairs	5	6	4	5	N/A	N/A
		Maximum I/O per Pair	8	9	9	10	N/A	N/A
CSG324	LX	V _{CCO} /GND Pairs	6	6	6	6	N/A	N/A
		Maximum I/O per Pair	10	9	10	9	N/A	N/A
	LXT	V _{CCO} /GND Pairs	4	6	6	6	N/A	N/A
		Maximum I/O per Pair	4	9	10	9	N/A	N/A
CS(G)484	LX	V _{CCO} /GND Pairs	8	13	8	13	N/A	N/A
		Maximum I/O per Pair	7	8	7	8	N/A	N/A
	LXT	V _{CCO} /GND Pairs	7	12	8	13	N/A	N/A
		Maximum I/O per Pair	5	8	6	8	N/A	N/A
FG(G)484	LX	V _{CCO} /GND Pairs	10	10	11	11	N/A	N/A
		Maximum I/O per Pair	6	8	9	8	N/A	N/A
	LXT	V _{CCO} /GND Pairs	6	10	11	10	N/A	N/A
		Maximum I/O per Pair	7	8	7	8	N/A	N/A
FG(G)676	LX45	V _{CCO} /GND Pairs	12	15	10	16	N/A	N/A
		Maximum I/O per Pair	3	7	8	7	N/A	N/A
	LX75, LX100, LX150	V _{CCO} /GND Pairs	12	9	10	10	6	6
		Maximum I/O per Pair	9	10	9	9	8	9
	LXT	V _{CCO} /GND Pairs	10	8	10	8	7	7
		Maximum I/O per Pair	8	7	8	8	7	7
FG(G)900	LX	V _{CCO} /GND Pairs	17	14	17	14	7	8
		Maximum I/O per Pair	7	6	7	8	7	6
	LXT	V _{CCO} /GND Pairs	15	14	13	14	7	8
		Maximum I/O per Pair	7	6	8	8	7	6

Table 34: SSO Limit per V_{CCO}/GND Pair (Cont'd)

V_{CCO}	I/O Standard	Drive	Slew	SSO Limit per V_{CCO}/GND Pair			
				All TQG144, CPG196, CSG225, FT(G)256, and LX devices in CSG324		All CS(G)484, FG(G)484, FG(G)676, FG(G)900, and LXT devices in CSG324	
				Bank 0/2	Bank 1/3	Bank 0/2	Bank 1/3/4/5
Various	LVDS_33			16	N/A	16	N/A
	LVDS_25			20	N/A	20	N/A
	BLVDS_25			20	48	20	20
	MINI_LVDS_33			13	N/A	13	N/A
	MINI_LVDS_25			18	N/A	18	N/A
	RSDS_33			12	N/A	12	N/A
	RSDS_25			15	N/A	15	N/A
	TMDS_33			83	N/A	83	N/A
	PPDS_33			12	N/A	12	N/A
	PPDS_25			16	N/A	16	N/A
	DISPLAY_PORT			42	40	42	30
	I2C			47	55	47	42
	SMBUS			44	52	44	40

Notes:

- SSO limits greater than the number of I/O per V_{CCO}/GND pair (Table 33) indicate No Limit for the given I/O standard. They are provided in this table to calculate limits when using multiple I/O standards in a bank.
- Not available (N/A) indicates that the I/O standard is not available in the given bank.
- When used with the MCB, these signals are exempt from SSO analysis due to the known activity of the MCB switching patterns. SSO performance is validated for all MCB instances. MCB outputs can, in some cases, exceed the SSO limits.

Input/Output Delay Switching Characteristics

Table 39: IODELAY2 Switching Characteristics

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L ⁽³⁾	
$T_{\text{IODCCK_CAL}} / T_{\text{IODCKC_CAL}}$	CAL pin Setup/Hold with respect to CK	0.28/ -0.13	0.33/ -0.13	0.48/ -0.13	N/A	ns
$T_{\text{IODCCK_CE}} / T_{\text{IODCKC_CE}}$	CE pin Setup/Hold with respect to CK	0.17/ -0.03	0.17/ -0.03	0.25/ -0.02	N/A	ns
$T_{\text{IODCCK_INC}} / T_{\text{IODCKC_INC}}$	INC pin Setup/Hold with respect to CK	0.10/ 0.02	0.12/ 0.03	0.18/ 0.06	N/A	ns
$T_{\text{IODCCK_RST}} / T_{\text{IODCKC_RST}}$	RST pin Setup/Hold with respect to CK	0.12/ -0.02	0.15/ -0.02	0.22/ -0.01	N/A	ns
T_{TAP1} ⁽²⁾	Maximum tap 1 delay	8	14	16	N/A	ps
T_{TAP2}	Maximum tap 2 delay	40	66	77	N/A	ps
T_{TAP3}	Maximum tap 3 delay	95	120	140	N/A	ps
T_{TAP4}	Maximum tap 4 delay	108	141	166	N/A	ps
T_{TAP5}	Maximum tap 5 delay	171	194	231	N/A	ps
T_{TAP6}	Maximum tap 6 delay	207	249	292	N/A	ps
T_{TAP7}	Maximum tap 7 delay	212	276	343	N/A	ps
T_{TAP8}	Maximum tap 8 delay	322	341	424	N/A	ps
F_{MINCAL}	Minimum allowed bit rate for calibration in variable mode: VARIABLE_FROM_ZERO, VARIABLE_FROM_HALF_MAX, and DIFF_PHASE_DETECTOR.	188	188	188	N/A	Mb/s
$T_{\text{IODDO_IDATAIN}}$	Propagation delay through IODELAY2	Note 1	Note 1	Note 1	Note 3	—
$T_{\text{IODDO_ODATAIN}}$	Propagation delay through IODELAY2	Note 1	Note 1	Note 1	Note 3	—

Notes:

- Delay depends on IODELAY2 tap setting. See TRACE report for actual values.
- Maximum delay = integer (number of taps/8) $\times$ T_{TAP8} + T_{TAPn} (where n equals the remainder). For minimum delay consult the TRACE setup and hold report. Minimum delay is typically greater than 30% of the maximum delay. Tap delays can vary by device and overall conditions. See TRACE report for actual values.
- Spartan-6 -1L devices only support tap 0. See TRACE report for actual values.

Block RAM Switching Characteristics

Table 43: Block RAM Switching Characteristics

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
Block RAM Clock to Out Delays						
T _{RCKO_DO}	Clock CLK to DOUT output (without output register) ⁽¹⁾	1.85	2.10	2.10	3.50	ns, Max
T _{RCKO_DO_REG}	Clock CLK to DOUT output (with output register) ⁽²⁾	1.60	1.75	1.75	2.30	ns, Max
Setup and Hold Times Before/After Clock CLK						
T _{RCCK_ADDR} /T _{RCKC_ADDR}	ADDR inputs for XC devices ⁽³⁾	0.35/ 0.10	0.40/ 0.12	0.40/ 0.12	0.50/ 0.15	ns, Min
	ADDR inputs for XA and XQ devices ⁽³⁾	0.35/ 0.17	N/A	0.40/ 0.17	0.50/ 0.15	ns, Min
T _{RDCK_DI} /T _{RCKD_DI}	DIN inputs ⁽⁴⁾	0.30/ 0.10	0.30/ 0.10	0.30/ 0.10	0.40/ 0.15	ns, Min
T _{RCCK_EN} /T _{RCKC_EN}	Block RAM Enable (EN) input	0.22/ 0.05	0.25/ 0.06	0.25/ 0.06	0.44/ 0.10	ns, Min
T _{RCCK_REGCE} /T _{RCKC_REGCE}	CE input of output register	0.20/ 0.10	0.20/ 0.10	0.20/ 0.10	0.28/ 0.15	ns, Min
T _{RCCK_WE} /T _{RCKC_WE}	Write Enable (WE) input	0.25/ 0.10	0.33/ 0.10	0.33/ 0.10	0.28/ 0.15	ns, Min
Maximum Frequency						
F _{MAX}	Block RAM in all modes	320	280	280	150	MHz

Notes:

1. T_{RCKO_DO} includes T_{RCKO_DOA} and T_{RCKO_DOPA} as well as the B port equivalent timing parameters.
2. $T_{RCKO_DO_REG}$ includes $T_{RCKO_DOA_REG}$ and $T_{RCKO_DOPA_REG}$ as well as the B port equivalent timing parameters.
3. The ADDR setup and hold must be met when EN is asserted (even when WE is deasserted). Otherwise, block RAM data corruption is possible.
4. T_{RDCK_DI} includes both A and B inputs as well as the parity inputs of A and B.

Table 54: Switching Characteristics for the Delay-Locked Loop (DLL)⁽¹⁾ (Cont'd)

Symbol	Description	Speed Grade								Units
		-3		-3N		-2		-1L		
		Min	Max	Min	Max	Min	Max	Min	Max	
LOCK_DLL ⁽³⁾	When using the DLL alone: The time from deassertion at the DCM's reset input to the rising transition at its LOCKED output. When the DCM is locked, the CLKIN and CLKFB signals are in phase. CLKIN_FREQ_DLL < 50 MHz.	–	5	–	5	–	5	–	5	ms
	When using the DLL alone: The time from deassertion at the DCM's reset input to the rising transition at its LOCKED output. When the DCM is locked, the CLKIN and CLKFB signals are in phase. CLKIN_FREQ_DLL > 50 MHz	–	0.60	–	0.60	–	0.60	–	0.60	ms
Delay Lines										
DCM_DELAY_STEP ⁽⁵⁾	Finest delay resolution, averaged over all steps.	10	40	10	40	10	40	10	40	ps

Notes:

1. The values in this table are based on the operating conditions described in Table 2 and Table 53.
2. Indicates the maximum amount of output jitter that the DCM adds to the jitter on the CLKIN input.
3. For optimal jitter tolerance and faster LOCK time, use the CLKIN_PERIOD attribute.
4. Some jitter and duty-cycle specifications include 1% of input clock period or 0.01 UI. For example, this data sheet specifies a maximum jitter of $\pm(1\% \text{ of CLKIN period} + 150 \text{ ps})$. Assuming that the CLKIN frequency is 100 MHz, the equivalent CLKIN period is 10 ns. Since 1% of 10 ns is 0.1 ns or 100 ps, the maximum jitter is $\pm(100 \text{ ps} + 150 \text{ ps}) = \pm 250 \text{ ps}$.
5. A typical delay step size is 23 ps.
6. The timing analysis tools use the CLK_FEEDBACK = 1X condition for the CLKIN_CLKFB_PHASE value (reported as phase error). When using CLK_FEEDBACK = 2X, add 100 ps to the phase error for the CLKIN_CLKFB_PHASE value (as shown in this table).

Table 55: Recommended Operating Conditions for the Digital Frequency Synthesizer (DFS)⁽¹⁾

Symbol	Description	Speed Grade								Units
		-3		-3N		-2		-1L		
		Min	Max	Min	Max	Min	Max	Min	Max	
Input Frequency Ranges ⁽²⁾										
CLKIN_FREQ_FX	Frequency for the CLKIN input. Also described as F _{CLKIN} .	0.5	375 ⁽³⁾	0.5	375 ⁽³⁾	0.5	333 ⁽³⁾	0.5	200 ⁽³⁾	MHz
Input Clock Jitter Tolerance ⁽⁴⁾										
CLKIN_CYC_JITT_FX_LF	Cycle-to-cycle jitter at the CLKIN input, based on CLKFX output frequency: FCLKFX < 150 MHz.	–	±300	–	±300	–	±300	–	±300	ps
CLKIN_CYC_JITT_FX_HF	Cycle-to-cycle jitter at the CLKIN input, based on CLKFX output frequency: FCLKFX > 150 MHz.	–	±150	–	±150	–	±150	–	±150	ps
CLKIN_PER_JITT_FX	Period jitter at the CLKIN input.	–	±1	–	±1	–	±1	–	±1	ns

Notes:

1. DFS specifications apply when using either of the DFS outputs (CLKFX or CLKFX180).
2. When using both DFS and DLL outputs on the same DCM, follow the more restrictive CLKIN_FREQ_DLL specifications in Table 53.
3. The CLKIN_DIVIDE_BY_2 attribute increases the effective input frequency range. When set to TRUE, the input clock frequency is divided by two as it enters the DCM. Input clock frequencies for the clock buffer being used can be increased up to the F_{MAX} (see Table 48 and Table 49 for BUFG and BUFGIO limits).
4. CLKIN input jitter beyond these limits can cause the DCM to lose LOCK.

Table 57: Switching Characteristics for the Digital Frequency Synthesizer DFS (DCM_CLKGEN)⁽¹⁾

Symbol	Description	Speed Grade								Units
		-3		-3N		-2		-1L		
		Min	Max	Min	Max	Min	Max	Min	Max	
Output Frequency Ranges (DCM_CLKGEN)										
CLKOUT_FREQ_FX	Frequency for the CLKFX and CLKFX180 outputs	5	375	5	375	5	333	5	200	MHz
CLKOUT_FREQ_FXDV	Frequency for the CLKFXDV output	0.15625	187.5	0.15625	187.5	0.15625	166.5	0.15625	100	MHz
Output Clock Jitter ⁽²⁾⁽³⁾										
CLKOUT_PER_JITT_FX	Period jitter at the CLKFX and CLKFX180 outputs.	Typical = ±[0.2% of CLKFX period + 100]								ps
CLKOUT_PER_JITT_FXDV	Period jitter at the CLKFXDV output.	Typical = ±[0.2% of CLKFX period + 100]								ps
CLKFX_FREEZE_VAR	CLKFX period change in free running oscillator mode at the same temperature. FCLKFX > 50 MHz	Maximum = ±3% of CLKFX period								ps
	CLKFX period change in free running oscillator mode at the same temperature. FCLKFX < 50 MHz	Maximum = ±5% of CLKFX period								ps
CLKFX_FREEZE_TEMP_SLOPE	CLKFX period will change in free_oscillator mode over temperature. Add to CLKFX_FREEZE_VAR to determine total CLKFX period change. Percentage change for CLKFX period over 1°C.	Maximum = 0.1								%/°C
Duty Cycle ⁽⁴⁾⁽⁵⁾										
CLKOUT_DUTY_CYCLE_FX	Duty cycle precision for the CLKFX and CLKFX180 outputs, including the BUFGMUX and clock tree duty-cycle distortion	Maximum = ±[1% of CLKFX period + 350]								ps
CLKOUT_DUTY_CYCLE_FXDV	Duty cycle precision for the CLKFXDV outputs, including the BUFGMUX and clock tree duty-cycle distortion	Maximum = ±[1% of CLKFX period + 350]								ps
Lock Time										
LOCK_FX ⁽²⁾	The time from deassertion at the DCM's Reset input to the rising transition at its LOCKED output. The DFS asserts LOCKED when the CLKFX, CLKFX180, and CLKFXDV signals are valid. Lock time requires CLKFX_DIVIDE < F _{IN} /(0.50 MHz) when: F _{CLKIN} < 50 MHz	—	50	—	50	—	50	—	50	ms
	when: F _{CLKIN} > 50 MHz	—	5	—	5	—	5	—	5	ms

Table 57: Switching Characteristics for the Digital Frequency Synthesizer DFS (DCM_CLKGEN)⁽¹⁾ (Cont'd)

Symbol	Description	Speed Grade								Units
		-3		-3N		-2		-1L		
		Min	Max	Min	Max	Min	Max	Min	Max	
Spread Spectrum										
F _{CLKIN_FIXED_SPREAD_SPECTRUM}	Frequency of the CLKIN input for fixed spread spectrum (SPREAD_SPECTRUM = CENTER_LOW_SPREAD/ CENTER_HIGH_SPREAD)	30	200	30	200	30	200	30	200	MHz
T _{CENTER_LOW_SPREAD} ⁽⁶⁾	Spread at the CLKFX output for fixed spread spectrum (SPREAD_SPECTRUM = CENTER_LOW_SPREAD)	Typical = $\frac{100}{\text{CLKFX_DIVIDE}}$ Maximum = 250								ps
T _{CENTER_HIGH_SPREAD} ⁽⁶⁾	Spread at the CLKFX output for fixed spread spectrum (SPREAD_SPECTRUM= CENTER_HIGH_SPREAD)	Typical = $\frac{240}{\text{CLKFX_DIVIDE}}$ Maximum = 400								ps
F _{MOD_FIXED_SPREAD_SPECTRUM} ⁽⁶⁾	Average modulation frequency when using fixed spread spectrum (SPREAD_SPECTRUM = CENTER_LOW_SPREAD / CENTER_HIGH_SPREAD)	Typical = F _{IN} /1024								MHz

Notes:

- The values in this table are based on the operating conditions described in Table 2 and Table 55.
- For optimal jitter tolerance and a faster LOCK time, use the CLKIN_PERIOD attribute.
- Output jitter is characterized with no input jitter. Output jitter strongly depends on the environment, including the number of SSOs, the output drive strength, CLB utilization, CLB switching activities, switching frequency, power supply, and PCB design. The actual maximum output jitter depends on the system application.
- The CLKFX, CLKFXDV, and CLKFX180 outputs have a duty cycle of approximately 50%.
- Some duty-cycle and alignment specifications include a percentage of the CLKFX output period. For example, this data sheet specifies a maximum CLKFX jitter of $\pm(1\% \text{ of CLKFX period} + 200 \text{ ps})$. Assuming that the CLKFX output frequency is 100 MHz, the equivalent CLKFX period is 10 ns, and 1% of 10 ns is 0.1 ns or 100 ps. Accordingly, the maximum jitter is $\pm(100 \text{ ps} + 200 \text{ ps}) = \pm 300 \text{ ps}$.
- When using CENTER_LOW_SPREAD, CENTER_HIGH_SPREAD, the valid values for CLKFX_MULTIPLY are limited to 2 through 32, and the valid values for CLKFX_DIVIDE are limited to 1 through 4.

Table 58: Recommended Operating Conditions for the Phase-Shift Clock in Variable Phase Mode (DCM_SP) or Dynamic Frequency Synthesis (DCM_CLKGEN)

Symbol	Description	Speed Grade								Units
		-3		-3N		-2		-1L		
		Min	Max	Min	Max	Min	Max	Min	Max	
Operating Frequency Ranges										
PSCLK_FREQ	Frequency for the PSCLK (DCM_SP) or PROGCLK (DCM_CLKGEN) input.	1	167	1	167	1	167	1	100	MHz
Input Pulse Requirements										
PSCLK_PULSE	PSCLK (DCM_SP) or PROGCLK (DCM_CLKGEN) pulse width as a percentage of the clock period.	40	60	40	60	40	60	40	60	%

Table 69: Global Clock Input to Output Delay With DCM and PLL in Source-Synchronous Mode

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
LVCMOS25 Global Clock Input to Output Delay using Output Flip-Flop, 12mA, Fast Slew Rate, <i>with</i> DCM in Source-Synchronous Mode and PLL in DCM2PLL Mode.							
T _{ICKOFDCM0_PLL}	Global Clock and OUTFF with DCM and PLL	XC6SLX4	5.58	N/A	7.42	8.54	ns
		XC6SLX9	5.58	6.19	7.42	8.54	ns
		XC6SLX16	5.50	6.06	7.05	8.24	ns
		XC6SLX25	5.57	6.04	7.02	8.33	ns
		XC6SLX25T	5.57	6.04	7.02	N/A	ns
		XC6SLX45	5.53	5.97	6.96	8.32	ns
		XC6SLX45T	5.53	5.97	6.96	N/A	ns
		XC6SLX75	5.55	6.00	6.99	8.54	ns
		XC6SLX75T	5.55	6.00	6.99	N/A	ns
		XC6SLX100	5.58	6.03	7.02	9.11	ns
		XC6SLX100T	5.62	6.03	7.02	N/A	ns
		XC6SLX150	5.32	5.70	6.41	8.26	ns
		XC6SLX150T	5.32	5.70	6.41	N/A	ns
		XA6SLX4	5.87	N/A	7.28	N/A	ns
		XA6SLX9	5.87	N/A	7.28	N/A	ns
		XA6SLX16	6.02	N/A	6.87	N/A	ns
		XA6SLX25	5.88	N/A	6.90	N/A	ns
		XA6SLX25T	5.88	N/A	7.00	N/A	ns
		XA6SLX45	5.82	N/A	6.81	N/A	ns
		XA6SLX45T	5.82	N/A	6.81	N/A	ns
		XA6SLX75	5.81	N/A	6.80	N/A	ns
		XA6SLX75T	5.81	N/A	6.80	N/A	ns
		XA6SLX100	N/A	N/A	6.88	N/A	ns
		XQ6SLX75	N/A	N/A	6.80	8.54	ns
		XQ6SLX75T	5.81	N/A	6.80	N/A	ns
		XQ6SLX150	N/A	N/A	6.41	8.26	ns
		XQ6SLX150T	5.90	N/A	6.41	N/A	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. DCM and PLL output jitter are already included in the timing calculation.

Spartan-6 Device Pin-to-Pin Input Parameter Guidelines

All devices are 100% functionally tested. The representative values for typical pin locations and normal clock loading are listed in Table 70 through Table 77. Values are expressed in nanoseconds unless otherwise noted.

Table 70: Global Clock Setup and Hold Without DCM or PLL (No Delay)

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for LVC MOS25 Standard.(1)							
T _{PSND} / T _{PHND}	No Delay Global Clock and IFF(3) without DCM or PLL	XC6SLX4	0.10/1.56	N/A	0.10/1.83	0.07/2.54	ns
		XC6SLX9	0.10/1.56	0.10/1.57	0.10/1.84	0.07/2.54	ns
		XC6SLX16	0.12/1.42	0.12/1.48	0.12/1.64	0.13/2.19	ns
		XC6SLX25	0.18/1.64	0.18/1.75	0.18/1.99	0.11/2.57	ns
		XC6SLX25T	0.18/1.64	0.18/1.75	0.18/1.99	N/A	ns
		XC6SLX45	-0.08/1.80	-0.08/1.95	-0.08/2.27	-0.17/2.74	ns
		XC6SLX45T	-0.08/1.80	-0.08/1.95	-0.08/2.27	N/A	ns
		XC6SLX75	0.13/1.81	0.13/2.06	0.13/2.27	-0.12/3.30	ns
		XC6SLX75T	0.13/1.81	0.13/2.06	0.13/2.27	N/A	ns
		XC6SLX100	-0.14/2.03	-0.14/2.24	-0.14/2.56	-0.17/3.44	ns
		XC6SLX100T	-0.14/2.03	-0.14/2.24	-0.14/2.56	N/A	ns
		XC6SLX150	-0.24/2.42	-0.24/2.74	-0.24/2.95	-0.60/3.75	ns
		XC6SLX150T	-0.24/2.42	-0.24/2.74	-0.24/2.95	N/A	ns
		XA6SLX4	0.10/1.57	N/A	0.10/1.84	N/A	ns
		XA6SLX9	0.10/1.57	N/A	0.10/1.84	N/A	ns
		XA6SLX16	0.12/1.43	N/A	0.12/1.64	N/A	ns
		XA6SLX25	0.18/1.65	N/A	0.18/1.99	N/A	ns
		XA6SLX25T	0.18/1.65	N/A	0.18/1.99	N/A	ns
		XA6SLX45	-0.08/1.82	N/A	-0.08/2.27	N/A	ns
		XA6SLX45T	-0.08/1.82	N/A	-0.08/2.27	N/A	ns
		XA6SLX75	0.13/2.02	N/A	0.13/2.32	N/A	ns
		XA6SLX75T	0.13/2.02	N/A	0.13/2.32	N/A	ns
		XA6SLX100	N/A	N/A	0.10/2.51	N/A	ns
		XQ6SLX75	N/A	N/A	0.13/2.32	-0.12/3.30	ns
		XQ6SLX75T	0.13/2.02	N/A	0.13/2.32	N/A	ns
		XQ6SLX150	N/A	N/A	-0.24/2.95	-0.60/3.75	ns
		XQ6SLX150T	-0.24/2.74	N/A	-0.24/2.95	N/A	ns

Notes:

- Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage.
- IFF = Input Flip-Flop or Latch.

Table 77: Global Clock Setup and Hold With DCM and PLL in Source-Synchronous Mode

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
Example Data Input Set-Up and Hold Times Relative to a Forwarded Clock Input Pin, ⁽¹⁾ Using DCM, PLL, and Global Clock Buffer for the LVCMOS25 standard.							
T _{PSDCMPLL_0} / T _{PHDCMPLL_0}	No Delay Global Clock and IFF ⁽²⁾ with DCM in Source-Synchronous Mode and PLL in DCM2PLL Mode.	XC6SLX4	0.43/1.07	N/A	0.43/1.43	1.10/1.67	ns
		XC6SLX9	0.43/1.03	0.45/1.14	0.45/1.43	1.10/1.67	ns
		XC6SLX16	0.74/0.93	0.74/1.12	0.74/1.21	0.77/1.35	ns
		XC6SLX25	0.67/1.02	0.76/1.11	0.84/1.18	1.23/1.46	ns
		XC6SLX25T	0.67/1.02	0.76/1.11	0.84/1.18	N/A	ns
		XC6SLX45	0.65/0.99	0.65/1.04	0.71/1.12	1.18/1.58	ns
		XC6SLX45T	0.65/1.00	0.65/1.04	0.71/1.12	N/A	ns
		XC6SLX75	0.86/1.01	0.88/1.06	0.94/1.14	1.29/1.67	ns
		XC6SLX75T	0.86/1.01	0.88/1.06	0.94/1.14	N/A	ns
		XC6SLX100	0.50/1.10	0.56/1.10	0.61/1.17	0.84/2.24	ns
		XC6SLX100T	0.50/1.10	0.56/1.10	0.61/1.17	N/A	ns
		XC6SLX150	0.45/1.28	0.47/1.28	0.52/1.28	1.27/1.56	ns
		XC6SLX150T	0.45/1.28	0.47/1.28	0.52/1.28	N/A	ns
		XA6SLX4	0.74/1.00	N/A	0.74/1.43	N/A	ns
		XA6SLX9	0.74/1.00	N/A	0.74/1.43	N/A	ns
		XA6SLX16	1.81/1.15	N/A	1.81/1.03	N/A	ns
		XA6SLX25	0.89/1.01	N/A	0.96/1.05	N/A	ns
		XA6SLX25T	0.89/1.01	N/A	1.04/1.15	N/A	ns
		XA6SLX45	0.69/0.95	N/A	0.83/0.96	N/A	ns
		XA6SLX45T	0.69/0.95	N/A	0.83/0.96	N/A	ns
		XA6SLX75	0.88/0.94	N/A	1.06/0.96	N/A	ns
		XA6SLX75T	0.88/0.94	N/A	1.06/0.96	N/A	ns
		XA6SLX100	N/A	N/A	1.55/1.33	N/A	ns
		XQ6SLX75	N/A	N/A	1.06/0.96	1.29/1.67	ns
		XQ6SLX75T	0.88/0.94	N/A	1.06/0.96	N/A	ns
		XQ6SLX150	N/A	N/A	0.64/1.30	1.27/1.56	ns
		XQ6SLX150T	0.58/1.30	N/A	0.64/1.30	N/A	ns

Notes:

- Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage. The timing values were measured using the fine-phase adjustment feature of the DCM. These measurements include CMT jitter; DCM CLK0 driving PLL, PLL CLKOUT0 driving BUFG. Package skew is not included in these measurements.
- IFF = Input Flip-Flop

Date	Version	Description of Revisions
06/14/10	1.5	In Table 2, added note 5 and added temperature range to V_{FS} and R_{FUSE}. Removed speed grade delineation, revised I_{RPD} description, and updated note 2 in Table 4. Added note 2 to Table 7. Added $DIFF_MOBILE_DDR$ to Table 8 and Table 10. Added note 4 to Table 15. Changed minimum DV_{PPIN} in Table 16. Updated $F_{GTPDRCLK}$ in Table 19. Increased maximum T_{LLSKEW} in Table 22. Updated descriptions and added data to Table 23. Removed note 1 and added new data to the Networking Applications section in Table 25. Updated Table 26 and Table 27 to the data in ISE v12.1 software with speed specification v1.08. In Table 28, added $DIFF_MOBILE_DDR$ and updated -4 speed grade data. Updated the maximum I/O pairs per bank in Table 33. Updated note 2 on Table 39. Revised the F_{MAX} in Table 44. In Table 47, updated description for $T_{SMCKCSO}$, revised values for T_{POR} and added Min value, added $T_{BPIICCK}$ and $T_{SPIICCK}$. Also in Table 47, added device dependencies to F_{SMCKCK} and F_{RBCKCK}. Updated and added data to Table 63 through Table 78, and Table 81. In Table 79, added data on the XC6SLX45-FG(G)676 and revised the XC6SLX45T and XC6SLX150T values. The following changes to this specification are addressed in the product change notice XC6SLX45-FG(G)676, <i>MCB Performance and JTAG Revision Code for Spartan-6 LX16 and LX45 FPGAs</i>. In Table 2, revised the V_{CCINT} to add the memory controller block extended performance specifications. In Table 25, changed the standard specifications and added extended performance specifications for the memory controller block and note 2. Added note 4 and updated values in Table 34.
06/24/10	1.6	Production release of XC6SLX45T (-2 and -3 speed grades), XC6SLX16 and XC6SLX45 (-3 speed grade) devices which includes changes to Table 26 and Table 27 (ISE v12.1 software with speed specification v1.08). Added the -3N speed grade, which designates Spartan-6 devices that do not support MCB functionality. This includes changes to Table 2 (note 2), Table 25 (note 4), and Switching Characteristics (Table 26). Updated Simultaneously Switching Outputs discussion. Added -3 speed grade values for T_{TAP} and F_{MINCAL} values in Table 39. In Table 40, updated T_{RPW} (-2 and -3 speed grade) values and F_{TOG} (-3 speed grade) values. In Table 48, updated T_{GIO} (-2 and -3 speed grade) values. Updated -3 values in spread spectrum section of Table 57.
07/16/10	1.7	Production release of specific devices listed in Table 26 and Table 27 using ISE v12.2 software with speed specification v1.11. Added note 4 advising designers of the patch which contains v1.11. Also updated the -1L speed specification to v1.04. Updated numerous -4 and -1L values. Added -4 T_{TAP} values and F_{MINCAL} to Table 39. Revised T_{CINCK}/T_{CKCIN} in Table 40. In Table 41, revised T_{SHCKO}. In Table 42, revised T_{REQ}. Added new -1L values to Table 47. Added and updated values in Table 79.
07/26/10	1.8	Production release of XC6SLX25, XC6SLX25T, XC6SLX100 and XC6SLX100T in the specific speed grades listed in Table 26 and Table 27 using ISE v12.2 software with speed specification v1.11. Added note 7 to Table 2 and moved V_{FS} and R_{FUSE} to a new Table 3. Added I_{HS} and note 4 to Table 4. Added note 1 to Table 28. Added and updated SSO limits per V_{CCO}/GND pairs in Table 34. Added note 3 to Table 47. In Table 54, removed -1L specifications for $CLKOUT_PER_JITT_DV1/2$ and revised $CLKIN_CLKFB_PHASE$ and $CLKOUT_PHASE_DLL$ values. Updated note 3 in both Table 56 and Table 57.
08/23/10	1.9	Updated values for $F_{GTPRANGE1}$, $F_{GTPRANGE2}$, and $F_{GPLLMIN}$ in Table 18. Revised -3 and -4 values in Table 21. Removed the -1L speed grade readback support restriction and note 3 in Table 47.
11/05/10	1.10	Production release of XC6SLX4 and XC6SLX9 in the specific speed grades listed in Table 26 and Table 27 using ISE v12.3 software with speed specification v1.12 for the -2 speed grade available in the 12.3 <i>Speed Files Patch</i>. Added note 3 advising designers of the patch which contains v1.12. In Table 2, added note 4. In Table 4, added note 2. In Table 10, added notes 2 and 3. In Table 44, added note 2. In Table 47, updated symbol for $T_{SMWCKCK}/T_{SMCKCKW}$, changed -1L values for $T_{USERCCLKH}$ and $T_{USERCCLKL}$, and added and revised the modes for F_{MCKCK} and F_{SMCKCK}. In Table 53, redefined and expanded description for $CLKIN_FREQ_DLL$ and rewrote note 3. Updated title of Table 58. Also in Table 78, revised T_{DCD_CLK} for XC6SLX150 and XC6SLX150T. Changed description of T_{PSFD}/T_{PHFD} in Table 71. For the -1L speed grade, updated data sheet to ISE 12.3 software with speed specification v1.05 which revised the values in the following tables: Table 25, Table 28, Table 35, Table 36, Table 37, Table 40 through Table 43, Table 48 through Table 56, Table 62 through Table 78, Table 80, and Table 81. Updated Notice of Disclaimer.

Date	Version	Description of Revisions
09/14/11	2.4	Production release of the XA6SLX4 and XA6SLX9 devices in Table 26 and Table 27 using ISE v13.2 software with -2 and -3 speed specification v1.19. Added production released version of the XA6SLX100 to Table 26 and Table 27 using ISE v13.3 software with -2 speed specification v1.20. Updated R_{OUT_TERM} description in Table 4. Fixed the LVPECL V_H error in Table 31. Updated introduction in Simultaneously Switching Outputs. Added the XA6SLX100 to Table 63 through Table 78, and Table 81. Added Note 4 to Table 78 because the T_{CKSKEW} for the XC6SLX100 is not the same as the T_{CKSKEW} for the XA6SLX100. Revised the revision history for version 1.6 dated 06/24/10. Removed the parenthetical statement about the -3N speed grade: (specifications are identical to the -3 speed grade).
10/17/11	3.0	Changed the data sheet from Preliminary Product Specification to Product Specification. Updated the Switching Characteristics, page 19 speed specification version ISE v13.3 software to -2 and -3 speed specification v1.20 and -1L speed specification of v1.08. Also updated Note 1 in Table 27. In Table 43, <i>Block RAM Switching Characteristics</i>, the F_{MAX} value for the -2 speed grade has been changed from 260 MHz to 280 MHz. In Table 54, <i>Switching Characteristics for the DLL</i>, a Note 6 was added and linked to CLKIN_CLKFB_PHASE.